

31. (Canceled) An dynamic random access memory device comprising:
an electrode which comprises:
- a) a first portion formed in an insulative layer;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
 - c) a third portion overlying said second portion and at least a portion of said insulative layer, wherein said first portion and said second portion are different materials.
- 32.(Canceled) The electrode as specified in Claim 31, wherein said second portion and said third portion are different materials.
- 33.(Canceled) The electrode as specified in Claim 32, wherein said first portion and said third portion are different materials.
- 34.(Canceled) An dynamic random access memory device comprising:
a capacitor which comprises:
- a) a first portion formed in an insulative layer;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
 - c) a third portion overlying said second portion and at least a portion of said insulative layer, wherein said first portion and said second portion are different materials.
- 35.(Canceled) The electrode as specified in Claim 34, wherein said second portion and said third portion are different materials.
- 36.(Canceled) The electrode as specified in Claim 35, wherein said first portion and said third portion are different materials.

37.(Canceled) The dynamic random access memory device as specified in Claim 34, further comprising a transistor.

38.(Canceled) The dynamic random access memory device as specified in Claim 34, further comprising:

- a) a dielectric layer overlying said third portion; and
- b) a cell plate electrode overlying said dielectric layer.

39. (Amended) An electrode comprising:

- a) a first portion formed in an insulative layer;
- b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
- c) a third portion overlying said second portion[and], extending above and below an upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion are different materials.

40. The electrode as specified in Claim 39, wherein said second portion and said third portion are different materials.

~~42.~~ The electrode as specified in Claim 39, further comprising a fourth portion interposed between said first and said second portions.

~~43.~~ The electrode as specified in Claim 42, wherein the fourth portion reduces contact resistance between said first and said second portions.

44. The electrode as specified in Claim 39, wherein said first portion is a silicon contact.

45. The electrode as specified in Claim 39, wherein said second portion is a diffusion barrier layer prohibiting diffusion of atoms between said first and said second portions.

46. The electrode as specified in Claim 39, wherein said third portion is an oxidation resistant layer.
47. The electrode as specified in Claim 39, wherein said insulative layer surrounds a lower sidewall of said third portion.
48. (Amended) A dynamic random access memory device comprising:
an electrode which comprises:
- a) a first portion formed in an insulative layer;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
 - c) a third portion overlying said second portion[and], extending above and below an upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion are different materials.
49. The electrode as specified in Claim 48, wherein said second portion and said third portion are different materials.
50. The electrode as specified in Claim 49, wherein said first portion and said third portion are different materials.
51. (Amended) A dynamic random access memory device comprising:
a capacitor which comprises:
- a) a first portion formed in an insulative layer;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
 - c) a third portion overlying said second portion[and], extending above and below an upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion are different materials.

52. The electrode as specified in Claim 51, wherein said second portion and said third portion are different materials.
53. The electrode as specified in Claim 52, wherein said first portion and said third portion are different materials.
54. The dynamic random access memory device as specified in Claim 51, further comprising:
- a) a dielectric layer overlying said third portion; and
 - b) a cell plate electrode overlying said dielectric layer.
55. The dynamic random access memory device as specified in Claim 51 further comprising a transistor.
56. (Amended) An electrode comprising:
- a) a contact formed in an insulative layer;
 - b) a diffusion barrier portion overlying said contact, said insulative layer surrounding a sidewall of said diffusion barrier portion; and
 - c) an oxidation resistant portion overlying said diffusion barrier portion[and], extending above and below an upper surface of said insulative layer, and including a recess, said diffusion barrier portion configured to inhibit diffusion of atoms between said contact and said oxidation resistant portion.
57. The electrode as specified in Claim 56, further comprising a reducing contact resistance portion interposed between said contact and said diffusion barrier portion, said reducing contact resistance portion configured to reduce a contact resistance between said contact and said diffusion barrier portion.

88. (New) An electrode comprising:
- a) a first portion formed in an insulative layer;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
 - c) a third portion overlying said second portion, extending above and below an upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion respectively consist essentially of polysilicon and tantalum.

89. (New) The electrode as specified in Claim 88, wherein said third portion consist essentially of platinum.

90. (New) An electrode comprising:
- a) a first portion formed in an insulative layer;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
 - c) a third portion overlying said second portion, extending above and below an upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion respectively consist essentially of polysilicon and titanium silicide.

91. (New) The electrode as specified in Claim 90, wherein said third portion consist essentially of platinum.

92. (New) An electrode comprising:
- a) a first portion formed in an insulative layer;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion; and
 - c) a third portion overlying said second portion, extending above and below an upper surface of said insulative layer, and including a recess; and